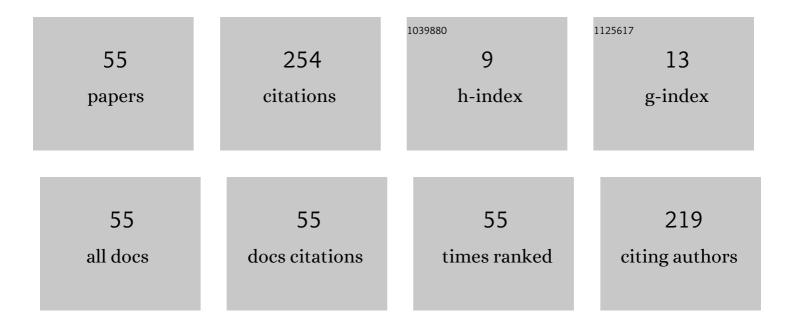
## Nobuo Satoh

List of Publications by Year in descending order

Source: https://exaly.com/author-pdf/982355/publications.pdf Version: 2024-02-01



NOBUO SATOH

#	Article	IF	CITATIONS
1	Design of Isolated Class-Φ <sub>2</sub> DC-DC Converter Based on Harmonic Analysis Technology. IEEJ Transactions on Industry Applications, 2022, 142, 177-186.	0.1	1
2	Observation of Power MOSFET Composed of Silicon Carbide with a Planar Type in the Voltage Applying State Using a Scanning Probe Microscope. IEEJ Transactions on Sensors and Micromachines, 2021, 141, 349-355.	0.0	1
3	Photo radiation pressure at resonance of frequency modulated micro cantilever. Nonlinear Theory and Its Applications IEICE, 2021, 12, 718-725.	0.4	1
4	Design of isolated class-Φ <sub>2</sub> DC-DC converter based on harmonic analysis technology. , 2021, , .		2
5	Evaluation of silicon carbide Schottky barrier diode within guard ring by multifunctional scanning probe microscopy. Japanese Journal of Applied Physics, 2020, 59, SN1014.	0.8	1
6	Development of scanning capacitance force microscopy using the dissipative force modulation method. Measurement Science and Technology, 2020, 31, 035904.	1.4	0
7	A Study on MHz Switching Operation in Flyback Converter for Lithium Ion Battery and its Parallelization. , 2020, , .		1
8	Investigation of power semiconductor devices under applying voltage by multi-purpose scanning probe microscope. , 2020, , .		0
9	HESO: A Heterogeneous Energy Spreading Object - An Application of Power Packet Technology to Mobile Vehicle , 2020, , .		1
10	Cross-sectional observation in nanoscale for Si power MOSFET by atomic force microscopy/Kelvin probe force microscopy/scanning capacitance force microscopy. Japanese Journal of Applied Physics, 2019, 58, SIIA04.	0.8	7
11	Nanoscale investigation of power semiconductor devices by scanning capacitance force microscopy. , 2019, , .		Ο
12	Development of atomic force microscopy combined with scanning electron microscopy for investigating electronic devices. AIP Advances, 2019, 9, .	0.6	3
13	Characterization of Polycrystalline Solar Cell by Scanning Laser Magnetic Microscopy. IEEJ Transactions on Sensors and Micromachines, 2019, 139, 335-340.	0.0	2
14	Investigation of an n <sup>â^'</sup> layer in a silicon fast recovery diode under applied bias voltages using Kelvin probe force microscopy. Japanese Journal of Applied Physics, 2018, 57, 08NB11.	0.8	4
15	Development of evaluation system for solar cell by scanning with lens-focused white LED illumination. , 2018, , .		1
16	Surface Potential Measurement of a Silicon Fast Recovery Diode under Applied Bias Voltages by Kelvin Probe Force Microscopy. , 2018, , .		0
17	Nanoscale investigation of bulk heterojunction organic solar cell by scanning capacitance force microscopy. Japanese Journal of Applied Physics, 2018, 57, 08NB05.	0.8	4
18	Nanoscale investigation of the silicon carbide double-diffused MOSFET with scanning capacitance force microscopy. Japanese Journal of Applied Physics, 2018, 57, 08NB09.	0.8	9

Νοβυο Σάτοη

#	Article	IF	CITATIONS
19	Driven by complementary operation of SiC-MOSFET and SiC-JFET within isolated flyback converter circuit. Nonlinear Theory and Its Applications IEICE, 2018, 9, 337-343.	0.4	5
20	Observation of silicon carbide Schottky barrier diode under applied reverse bias using atomic force microscopy/Kelvin probe force microscopy/scanning capacitance force microscopy. Japanese Journal of Applied Physics, 2017, 56, 08LB05.	0.8	11
21	A flyback converter using power-MOSFETs to achieve high-frequency operation beyond 10MHz. , 2017, , .		0
22	Nanoscale observation of organic thin film by atomic force microscopy. Japanese Journal of Applied Physics, 2017, 56, 08LB08.	0.8	2
23	Near-field light detection of a photo induced force by atomic force microscopy with frequency modulation. Japanese Journal of Applied Physics, 2017, 56, 08LB03.	0.8	1
24	Using dynamic force microscopy with piezoelectric cantilever for indentation and high-speed observation. Nonlinear Theory and Its Applications IEICE, 2017, 8, 98-106.	0.4	1
25	Evaluation of carrier concentration reduction in GaN-on-GaN wafers by Raman spectroscopy and Kelvin force microscopy. Japanese Journal of Applied Physics, 2017, 56, 08LB07.	0.8	4
26	Surface potential measurement of n-type organic semiconductor thin films by mist deposition via Kelvin probe microscopy. Japanese Journal of Applied Physics, 2017, 56, 08LB04.	0.8	1
27	Non-resonant frequency components observed in a dynamic Atomic Force Microscope. Nonlinear Theory and Its Applications IEICE, 2017, 8, 118-128.	0.4	4
28	Overview of Crystal for Power Devices. Journal of the Institute of Electrical Engineers of Japan, 2017, 137, 673-674.	0.0	0
29	Twinâ€Probe Atomic Force Microscopy with Optical Beam Deflection Using Vertically Incident Lasers by Two Beam Splitter. Electronics and Communications in Japan, 2016, 99, 92-100.	0.3	0
30	Optical and mechanical detection of near-field light by atomic force microscopy using a piezoelectric cantilever. Japanese Journal of Applied Physics, 2016, 55, 08NB04.	0.8	4
31	Investigation of the depletion layer by scanning capacitance force microscopy with Kelvin probe force microscopy. Japanese Journal of Applied Physics, 2016, 55, 08NB10.	0.8	16
32	Surface Potential and Topography Measurements of Gallium Nitride on Sapphire by Scanning Probe Microscopy. IEEJ Transactions on Sensors and Micromachines, 2016, 136, 96-101.	0.0	1
33	Surface potential measurement of fullerene derivative/copper phthalocyanine on indium tin oxide electrode by Kelvin probe force microscopy. Japanese Journal of Applied Physics, 2015, 54, 08KF06.	0.8	2
34	Surface Potential Investigation of Fullerene Derivative Film on Platinum Electrode under UV Irradiation by Kelvin Probe Force Microscopy Using a Piezoelectric Cantilever. E-Journal of Surface Science and Nanotechnology, 2015, 13, 102-106.	0.1	3
35	Surface Potential Measurement of Organic Multi-layered Films on Electrodes by Kelvin Probe Force Microscopy. IEICE Transactions on Electronics, 2015, E98.C, 91-97.	0.3	3
36	A flyback converter using power MOSFET to achieve high frequency operation beyond 13.56 MHz. , 2015,		6

3

. .

Νοβμο Σάτοη

#	Article	IF	CITATIONS
37	Twin-probe Atomic Force Microscopy with Optical Beam Deflection using Vertically Incident Lasers by Two Beam Splitter. IEEJ Transactions on Sensors and Micromachines, 2015, 135, 135-141.	0.0	4
38	Surface potential measurement of fullerene/copper phthalocyanine films on indium tin oxide electrode by Kelvin probe force microscopy. Japanese Journal of Applied Physics, 2014, 53, 05FY03.	0.8	2
39	Scanning near-field optical microscopy system based on frequency-modulation atomic force microscopy using a piezoelectric cantilever. Japanese Journal of Applied Physics, 2014, 53, 125201.	0.8	12
40	Multi-Probe Atomic Force Microscopy Using Piezo-Resistive Cantilevers and Interaction between Probes. E-Journal of Surface Science and Nanotechnology, 2013, 11, 13-17.	0.1	2
41	Energy Band Diagram near the Interface of Aluminum Oxide on p-Si Fabricated by Atomic Layer Deposition without/with Rapid Thermal Cycle Annealing Determined by Capacitance—Voltage Measurements. E-Journal of Surface Science and Nanotechnology, 2012, 10, 22-28.	0.1	5
42	Nanoscale liquid droplet deposition using the ultrasmall aperture on a dynamic mode AFM tip. Nanotechnology, 2011, 22, 175301.	1.3	17
43	Surface Potential Measurement of Tris(8-hydroxyquinolinato)aluminum and Bis[N-(1-naphthyl)-N-phenyl]benzidine Thin Films Fabricated on Indium–Tin Oxide by Kelvin Probe Force Microscopy. Japanese Journal of Applied Physics, 2011, 50, 071601.	0.8	3
44	Surface potential measurement of organic thin film on metal electrodes by dynamic force microscopy using a piezoelectric cantilever. Journal of Applied Physics, 2011, 109, 114306.	1.1	2
45	Surface Potential Measurement of Tris(8-hydroxyquinolinato)aluminum and Bis[N-(1-naphthyl)-N-phenyl]benzidine Thin Films Fabricated on Indium–Tin Oxide by Kelvin Probe Force Microscopy. Japanese Journal of Applied Physics, 2011, 50, 071601.	0.8	4
46	Near-field light detection by conservative and dissipative force modulation methods using a piezoelectric cantilever. Applied Physics Letters, 2010, 96, 233104.	1.5	9
47	Multi-Probe Atomic Force Microscopy with Optical Beam Deflection Method. Japanese Journal of Applied Physics, 2007, 46, 5636.	0.8	19
48	Multi-Probe Atomic Force Microscopy Using Piezoelectric Cantilevers. Japanese Journal of Applied Physics, 2007, 46, 5543.	0.8	22
49	Investigations of Nanoparticles by Scanning Near-Field Optical Microscopy Combined with Kelvin Probe Force Microscopy Using a Piezoelectric Cantilever. Japanese Journal of Applied Physics, 2004, 43, 4651-4654.	0.8	7
50	Nanoscale Investigation of Optical and Electrical Properties by Dynamic-Mode Atomic Force Microscopy Using a Piezoelectric Cantilever. Japanese Journal of Applied Physics, 2003, 42, 4878-4881.	0.8	21
51	Dynamic-mode AFM using the piezoelectric cantilever: investigations of local optical and electrical properties. Applied Surface Science, 2002, 188, 425-429.	3.1	13
52	Stress reduction and structural quality improvement due to In doping in GaAs/Si. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2000, 68, 166-170.	1.7	4
53	Internal carotid artery aneurysm with prominent calcification: Report of a case. Oral Radiology, 1992, 8, 73-78.	0.9	Ο
54	Embryoid bodies cultured in in vivo diffusion chambers show reduced tumorigenicity while retaining expression of F9 antigens. Experimental Cell Research, 1984, 153, 506-514.	1.2	4

#	Article	IF	CITATIONS
55	DIFFUSION CHAMBER CULTURE OF A SINGLE EMBRYOID BODY FROM THE TESTICULAR TERATOMA OF STRAIN 129 MOUSE. Development Growth and Differentiation, 1977, 19, 249-255.	0.6	2